

HRW0203A

Silicon Schottky Barrier Diode for Rectifying

HITACHI

ADE-208-014C (Z)

Rev 3

Oct. 1997

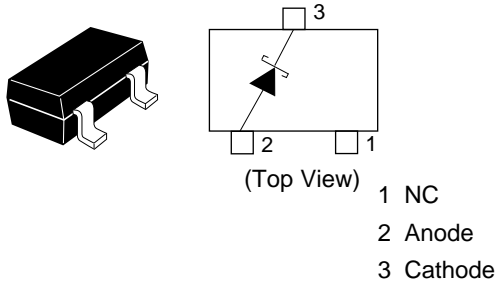
Features

- Low forward voltage drop and suitable for high efficiency rectifying.
- MPAK package is suitable for high density surface mounting and high speed assembly.

Ordering Information

Type No.	Laser Mark	Package Code
HRW0203A	S5	MPAK

Outline



Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Value	Unit
Repetitive peak reverse voltage	V_{RRM}^{*1}	30	V
Average rectified current	I_o^{*1}	200	mA
Non-Repetitive peak forward surge current	I_{FSM}^{*2}	2	A
Junction temperature	Tj	125	°C
Storage temperature	Tstg	-55~+125	°C

Note 1. See from Fig.1 to Fig.5, with polyimide board

Note 2. 50Hz sine wave 1 pulse

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	0.50	V	$I_F = 200 \text{ mA}$
Reverse current	I_R	—	—	50	μA	$V_R = 30\text{V}$
Capacitance	C	—	40	—	pF	$V_R = 0\text{V}, f = 1\text{MHz}$

Main Characteristic

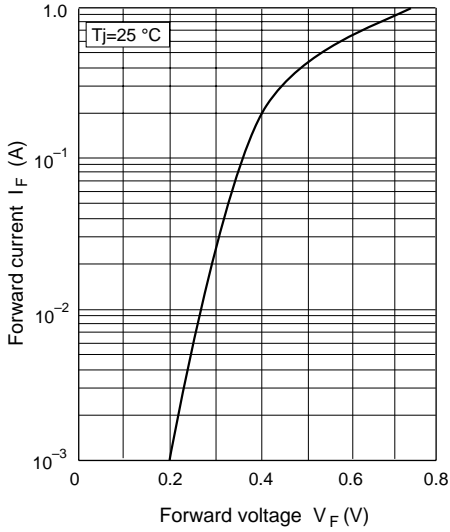


Fig.1 Forward current Vs. Forward voltage

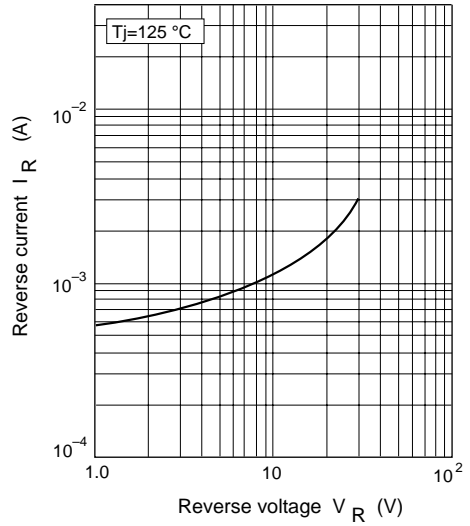


Fig.2 Reverse current Vs. Reverse voltage

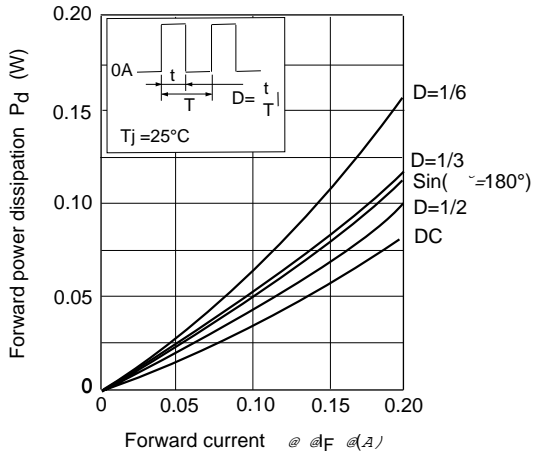


Fig.3. Forward power dissipation Vs. Forward current

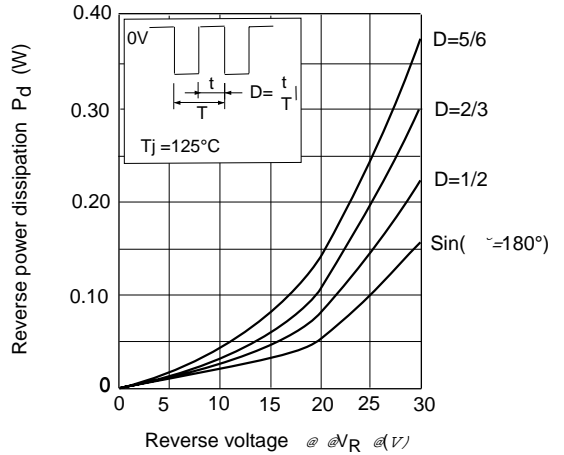


Fig.4. Reverse power dissipation Vs. Reverse voltage

Main Characteristic

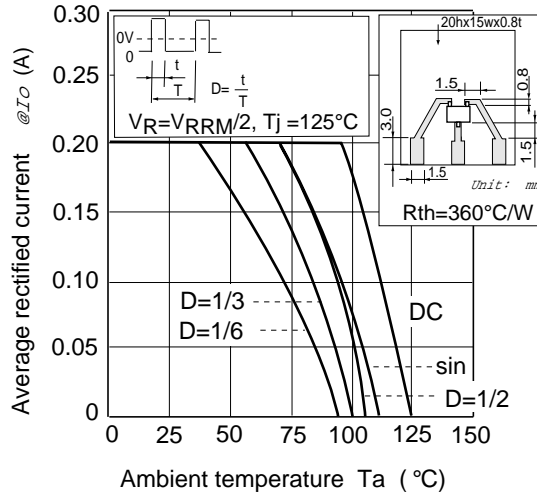


Fig.5 Average rectified current Vs. Ambient temperature

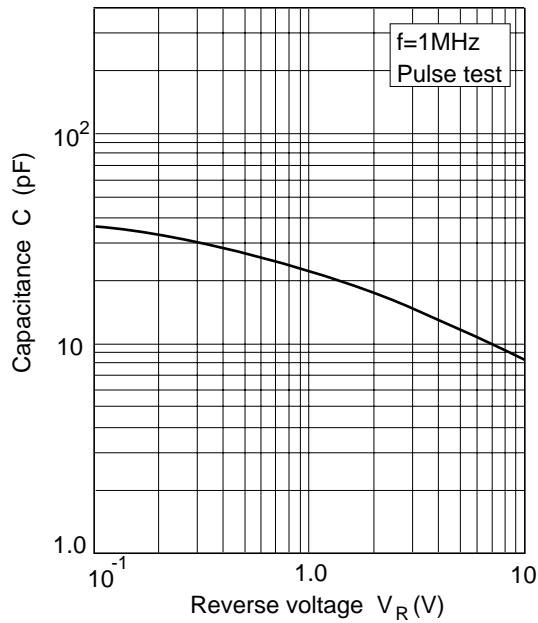
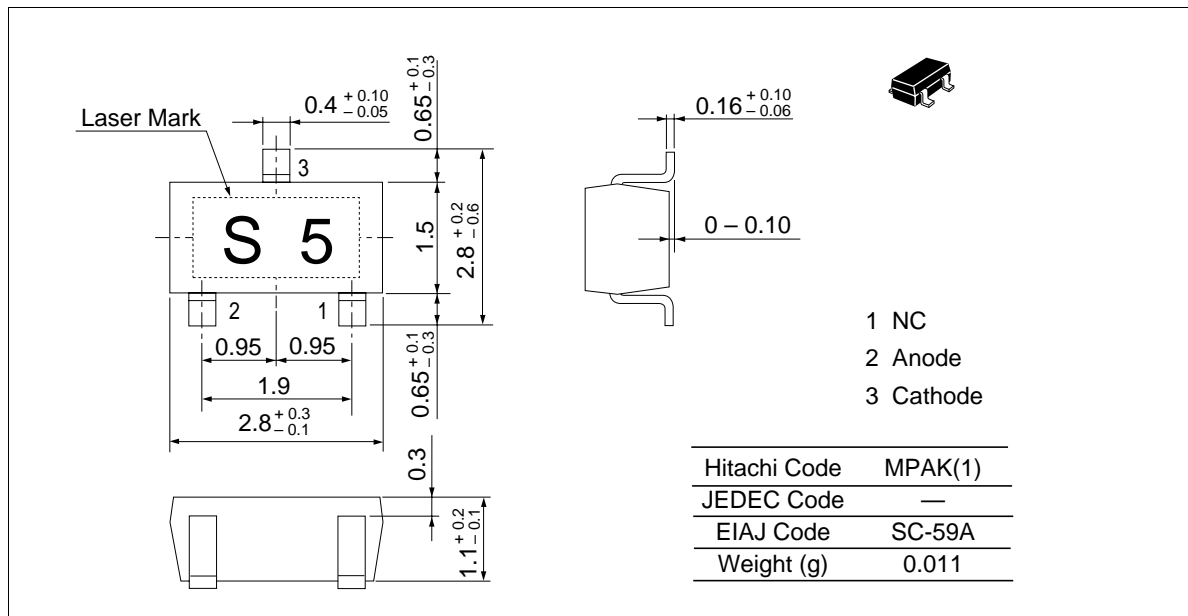


Fig.6 Capacitance Vs. Reverse voltage

Package Dimensions

Unit : mm



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